#### TOSHIBA TRANSISTOR SILICON, SILICON GERMANIUM NPN EPITAXIAL PLANAR TYPE

# MT6L67FS

#### VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

Two devices are built in to the fine pich small mold package (6pins):fs6

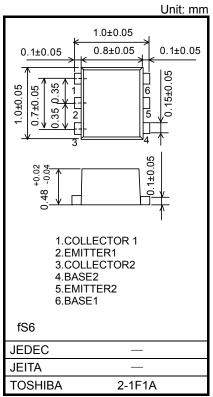
• It exsels in the buffer and oscillation use.

#### **Mounted Devices**

	Q1	Q2
Three-pin fSM mold products are corresponded	MT3S36FS	MT3S106FS

#### Absolute Maximum Ratings (Ta = 25°C)

CHARACTERISTICS	SYMBOL	RAT	UNIT	
CHARGETERISTICS		Q1	Q2	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	8	13	V
Collector-Emitter Voltage	V <sub>CEO</sub>	4.5	6	V
Emitter-Base Voltage	V <sub>EBO</sub>	1.5	1	V
Collector Current	Ι <sub>C</sub>	36	80	mA
Base Current	I <sub>B</sub>	18	20	mA
Collector power dissipation	P <sub>C</sub> (Note 1)	100		mW
		110 (Note 2)		
Junction temperature	Tj	125		°C
Storage temperature range	T <sub>stg</sub>	-55~125		°C



Weight: 0.001g (typ.)

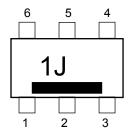
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

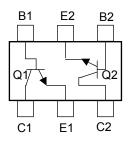
Note 1 : 10 mm<sup>2</sup>  $\times$  1.0 mm (t) at the time of glass epoxy printed circuit board mounting.

Note 2 : At the time of two-element operation

#### Marking (top view)



#### Pin Assignment (top view)



# ELECTRICAL CHARACTERISTICS Q1 (Ta = 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I <sub>CBO</sub>	$V_{CB} = 8 V, I_{E} = 0$		—	1	μA	
Emitter Cut-off Current	I <sub>EBO</sub>	$V_{EB} = 1 \text{ V}, \text{ I}_{C} = 0$	_		1	μA	
DC Current Gain	h <sub>FE</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$	70	_	140	_	
Reverse Transfer Capacitance	C <sub>re</sub> (Note)	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	0.21	0.4	pF	
Transition Frequency	f <sub>T</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 15 \text{ mA}$	16	20	_	GHz	
Insertion Gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE}$ = 3 V, $I_C$ = 15 mA, f = 1 GHz	16.5	18.5	_	dB	
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}, f = 2 \text{ GHz}$	10.5	13	_	uВ	
Noise Figure	NF	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 3 \text{ mA}, \text{ f} = 2 \text{ GHz}$	_	1.3	1.8	dB	

## ELECTRICAL CHARACTERISTICS Q2 (Ta = 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CBO</sub>	$V_{CB} = 5 V, I_{E} = 0$	_	_	0.1	μA
Emitter Cut-off Current	I <sub>EBO</sub>	$V_{EB} = 1 \text{ V}, \text{ I}_{C} = 0$	_	—	0.5	μA
DC Current Gain	h <sub>FE</sub>	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$	110	—	160	—
Reverse Transfer Capacitance	C <sub>re</sub> (Note)	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	0.5	0.7	pF
Transition Frequency	f <sub>T</sub>	$V_{CE} = 1 \text{ V}, I_{C} = 10 \text{ mA}$	6.5	8.5	—	GHz
Insertion Gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 10 \text{ mA}, \text{ f} = 2 \text{ GHz}$	_	8	—	dB
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 20 \text{ mA}, \text{ f} = 2 \text{ GHz}$	8.5	10	—	uБ
Noise Figure	NF	$V_{CE}$ = 1 V, I <sub>C</sub> = 10 mA, f = 2 GHz		1.2	2	dB

Note : C<sub>re</sub> is measured by 3 terminal method capacitance bridge.

## Caution

This device is sensitive to electrostatic discharge due to applied the high frequency transistor process of

fT=60GHz class is used for this product.

Please make enough tool and equipment earthed when you handle.

## **RESTRICTIONS ON PRODUCT USE**

20070701-EN GENERAL

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